

FH365P

P-Channel Enhancement Mode Power MOSFET

**Description**

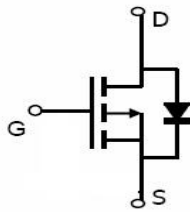
The FH365P uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge . This device is suitable for use as a load switch or in PWM applications.

**Application**

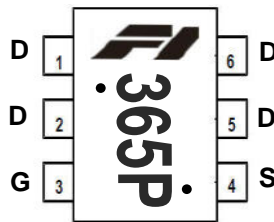
- PWM applications
- Load switch
- Power management

**General Features**

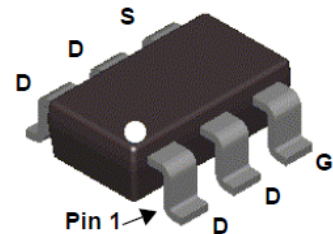
- $V_{DS} = -40V, I_D = -4.5A$   
 $R_{DS(ON)} < 54m\Omega @ V_{GS} = -10V$   
 $R_{DS(ON)} < 75m\Omega @ V_{GS} = -4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package



Schematic diagram



Marking and Pin Assignment



SOT23-6 top view

**Absolute Maximum Ratings (TA=25°C unless otherwise noted)**

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-40	V
Gate-Source Voltage	$V_{GS}$	±20	V
Drain Current-Continuous	$I_D$	-4.5	A
Drain Current-Pulsed (Note 1)	$I_{DM}$	-22	A
Maximum Power Dissipation	$P_D$	1.25	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

**Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	125	°C/W
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**Electrical Characteristics (TA=25 °C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-40	-45	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-40V, V_{GS}=0V$	-	-	-1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.1	-1.5	-1.9	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-4.0A$	-	45	54	m $\Omega$
		$V_{GS}=-4.5V, I_D=-3.0A$	-	62	75	
Forward Transconductance	$g_{FS}$	$V_{DS}=-5V, I_D=-4.0A$	-	10	-	S
<b>Dynamic Characteristics (Note4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-20V, V_{GS}=0V,$ $F=1.0MHz$	-	660	820	PF
Output Capacitance	$C_{oss}$		-	115	152	PF
Reverse Transfer Capacitance	$C_{rss}$		-	75	98	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-20V, I_D=-3.2A$ $V_{GS}=-10V, R_{GEN}=6\Omega$	-	7	-	nS
Turn-on Rise Time	$t_r$		-	3	-	nS
Turn-Off Delay Time	$t_{d(off)}$	$V_{DS}=-20V, I_D=-4A, V_{GS}=-4.5V$	-	30	-	nS
Turn-Off Fall Time	$t_f$		-	12	-	nS
Total Gate Charge	$Q_g$		-	9.5	-	nC
Gate-Source Charge	$Q_{gs}$	-	2	-	nC	
Gate-Drain Charge	$Q_{gd}$	-	3	-	nC	
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=-1A$	-	-	-1.2	V

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics



Figure 1: Switching Test Circuit

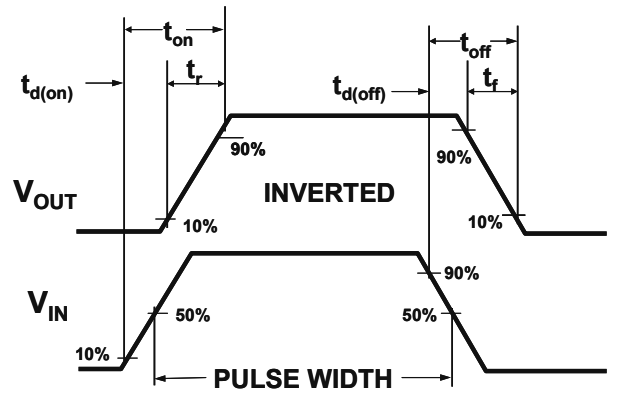
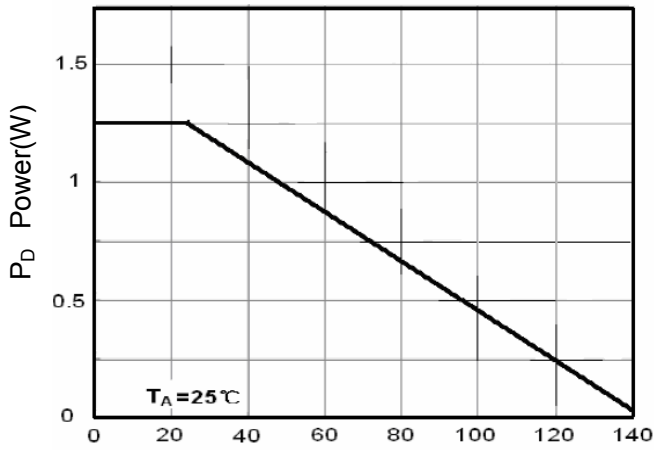
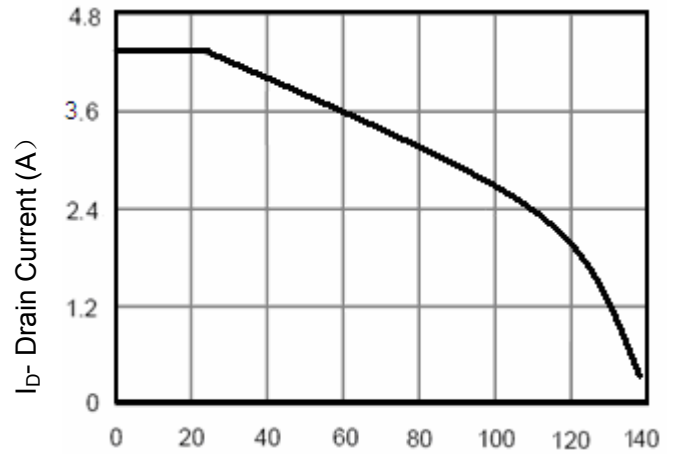


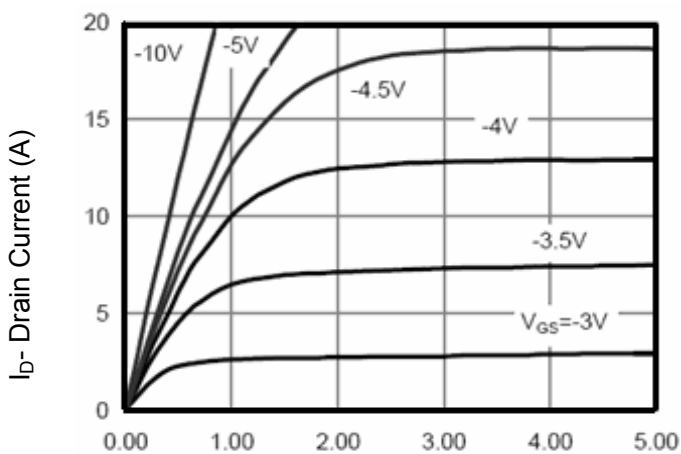
Figure 2: Switching Waveforms



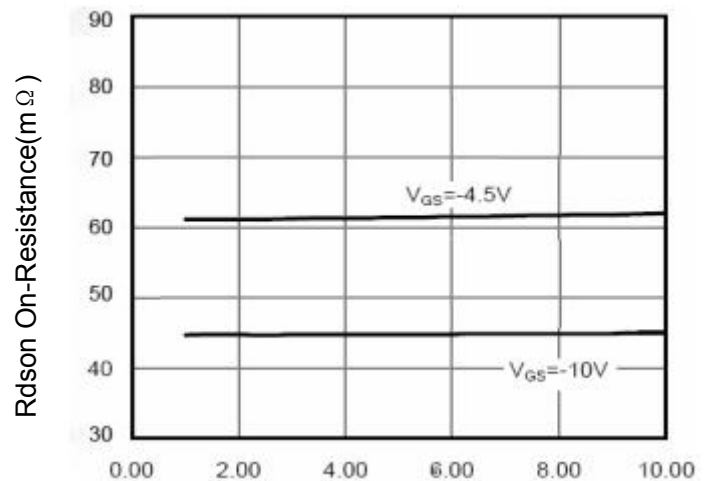
T<sub>J</sub>-Junction Temperature(°C)  
Figure 3 Power Dissipation



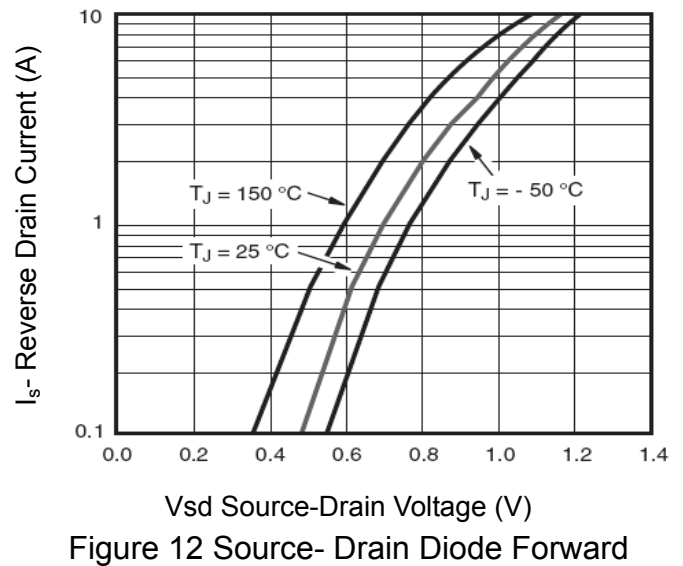
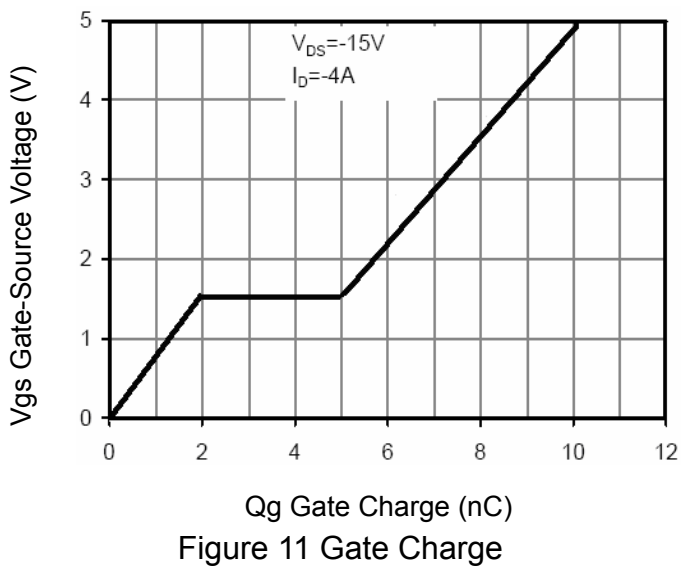
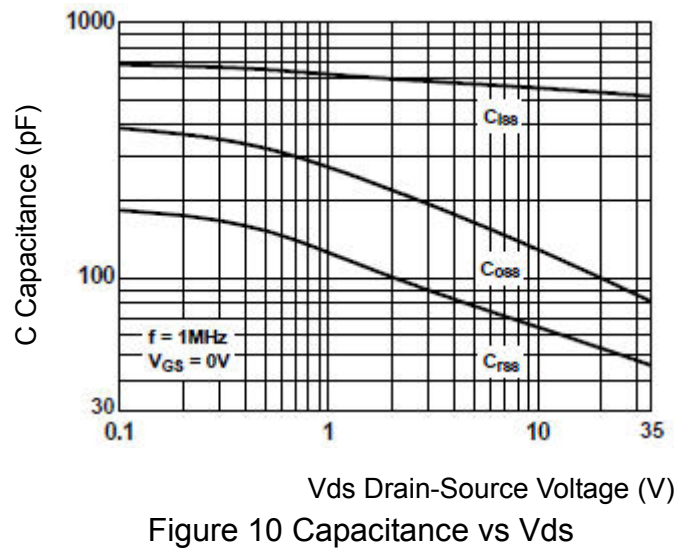
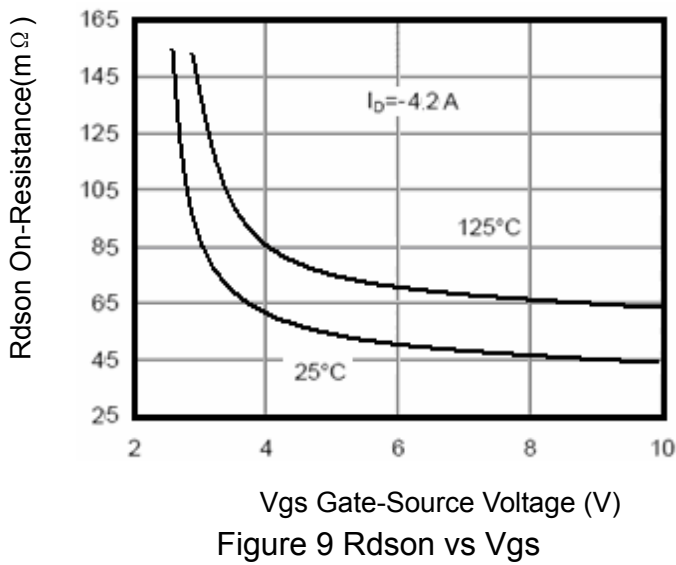
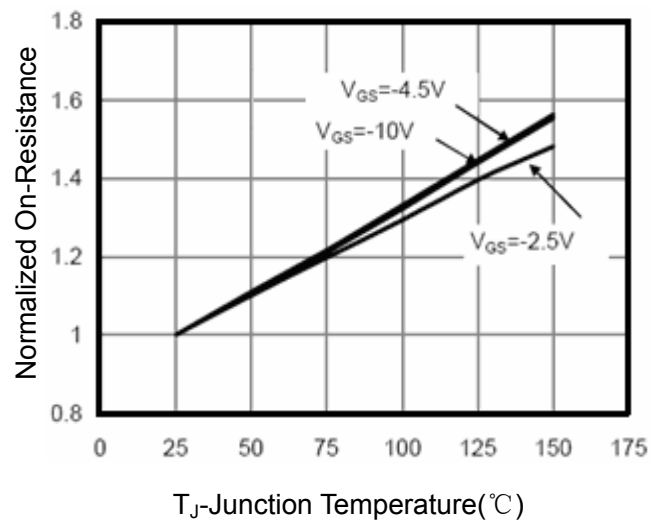
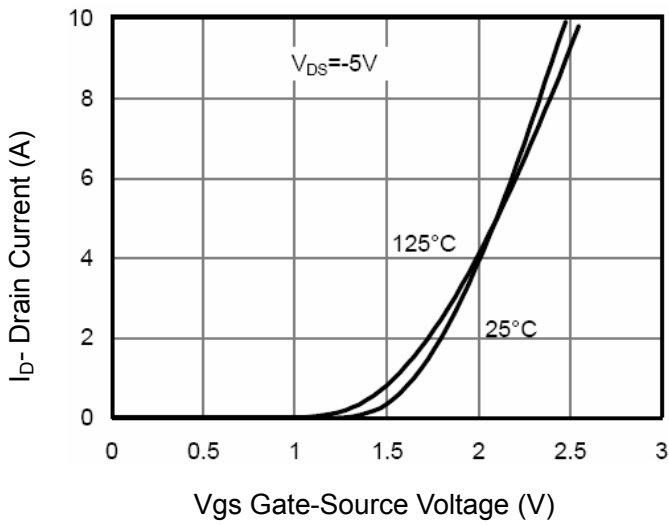
T<sub>J</sub>-Junction Temperature(°C)  
Figure 4 Drain Current



V<sub>ds</sub> Drain-Source Voltage (V)  
Figure 5 Output Characteristics



I<sub>D</sub>- Drain Current (A)  
Figure 6 Drain-Source On-Resistance



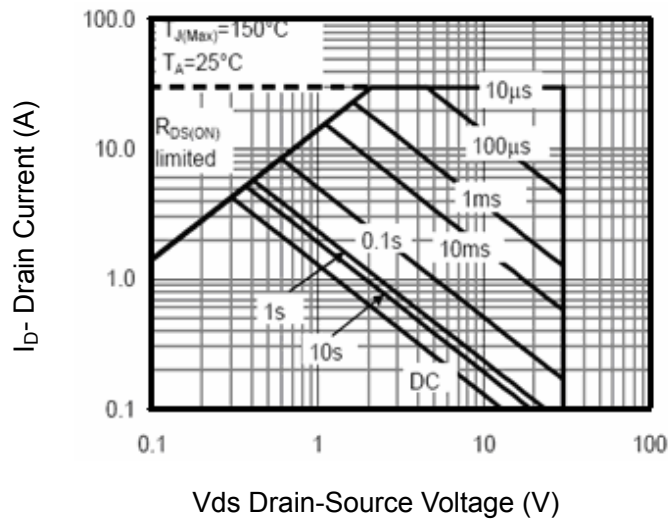


Figure 13 Safe Operation Area

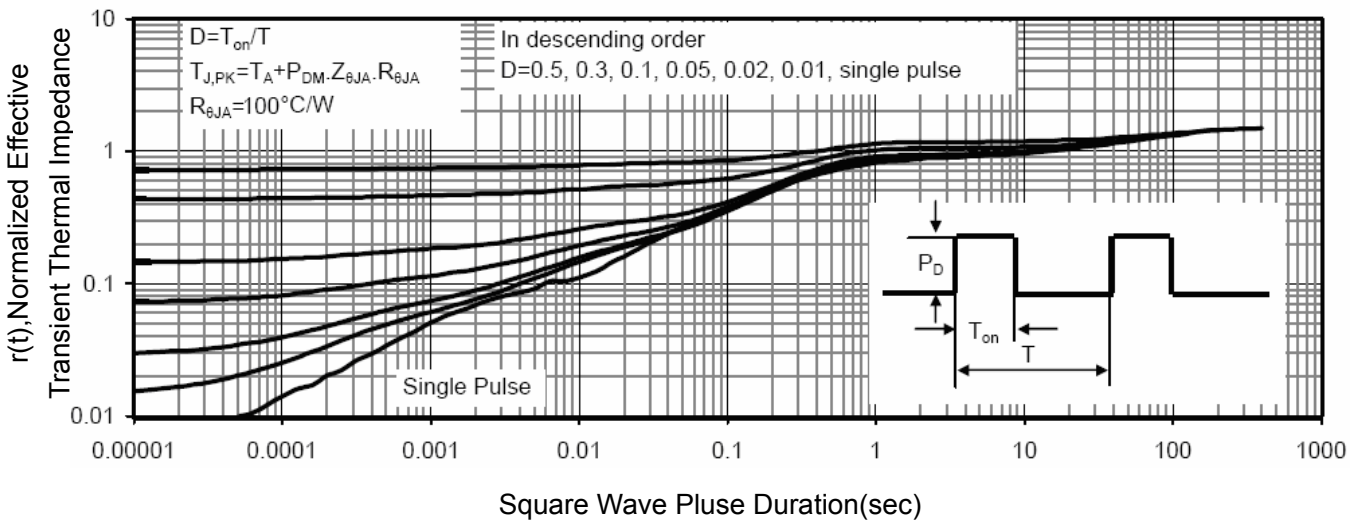
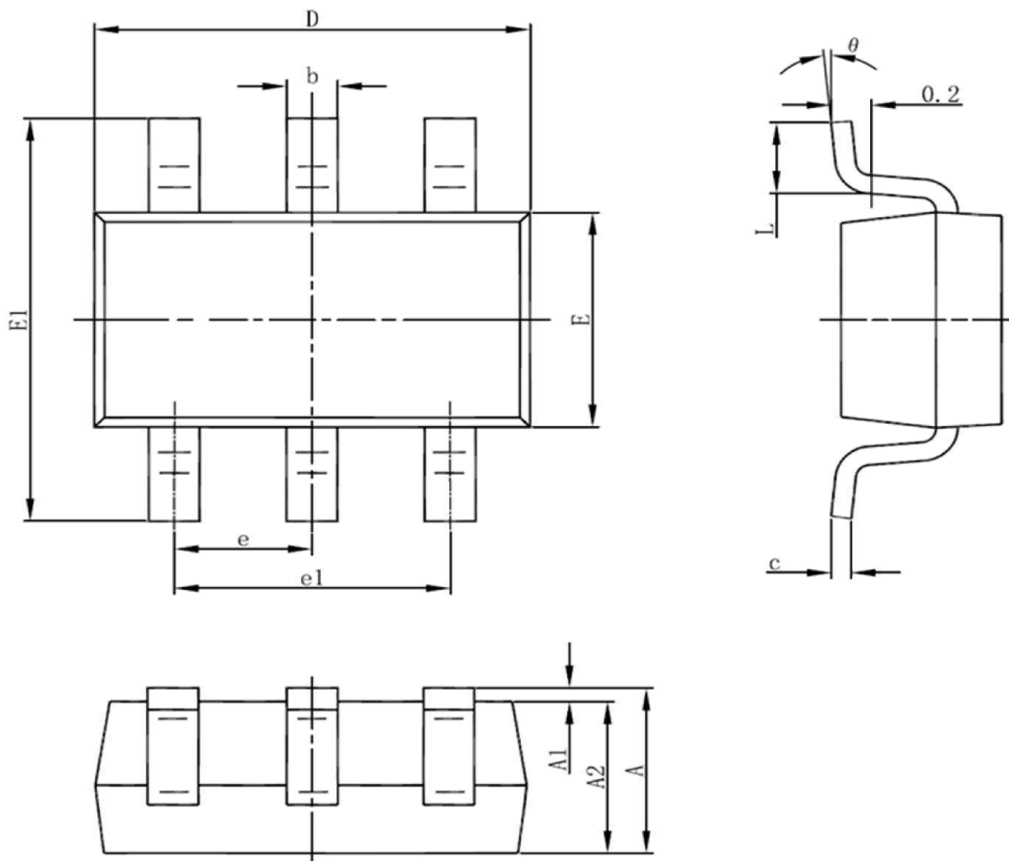


Figure 14 Normalized Maximum Transient Thermal Impedance

**Package Information : SOT23-6**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
$\theta$	0°	8°	0°	8°